

Page 14, line 2, change "a" to --the--.

Page 14, line 11, delete "a" and "an" (first occurrence).

Page 15, line 12, delete "a" (second occurrence).

Page 15, line 13, delete "position which is lower than".

Page 15, line 18, delete "a".

Page 15, line 25, delete "the position which is lower than".

Page 15, line 26, change "a" to --the--.

IN THE CLAIMS:

Please amend claims 1-3 and 7 as follows:

1. (Amended) A semiconductor device including both a large-diameter contact hole and a small-diameter contact hole formed to penetrate through an insulator film formed on a conductive portion to reach said conductive portion, said small-diameter contact hole being completely filled with a plug of a refractory conductive material, and said large-diameter contact hole [having a sidewall formed of] being partly filled by said refractory conductive material [on a side] which covers a sidewall surface of said large-diameter contact hole [, said sidewall covering said side surface lower than a position which is lower than an] to below the upper end of said large-diameter contact hole by a predetermined distance, a wiring conductor layer being deposited on said insulator film to cover a top surface of said plug of said refractory conductive material, and to fill [a] at least in part space remaining in said large-diameter contact hole thereby

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cont

to cover a bottom of said large-diameter contact hole and [a surface of said sidewall of] said refractory conductive material within said large-diameter contact hole.

a1

2. (Amended) A semiconductor device claimed in Claim 1 wherein each [of] said large-diameter contact hole and each said small-diameter contact hole has a funnel-shaped portion formed on an upper portion thereof to open or spread upward, a surface of said funnel-shaped portion being covered with said wiring conductor layer.

3. (Amended) A semiconductor device claimed in Claim ¹/₂ wherein said refractory conductive material is a material selected from the group consisting of a refractory metal and a silicide of a [refractor] refractory metal.

a2

7. (Amended) A semiconductor device claimed in Claim 1 wherein said refractory conductive material is a material selected from the group consisting of a refractory metal and a silicide of a [refractor] refractory metal.

IN THE ABSTRACT:

Please delete the Abstract presently standing in this application and insert in its place on a separate page the following new Abstract: